

10/525288

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

of 1

Complete if Known

Application Number	Not yet assigned 10/525,288
Filing Date	Herewith 02/16/2005
First Named Inventor	James S. Im
Art Unit	Not yet assigned 2813
Examiner Name	Not yet assigned Rodgers
Attorney Docket Number	A35076-PCT-USA (070050.2713)

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
					T ⁶

**Examiner
Signature**

Colleen E. Gray

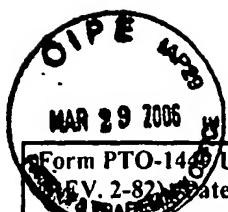
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Form PTO-146 U.S. Department of Commerce
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**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

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Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288
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Applicant James S. Im

Filing Date 02/16/2005	Group 2813
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Examiner <i>Rodgers</i>

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CR	2.	4234358	11/18/1980	Celler et al.
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CR	15.	4970546	11/1990	Suzuki et al.

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Examiner *Colleen E. O'Byrne*

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Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant James S. Im	
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		Examiner <i>Rodgers</i>	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
CR	16.	4977104	12/11/1990	Sawada et al.
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NY02:543906.1	Examiner <i>Colleen Grof</i>	Date Considered <i>23 March 2007</i>
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(CR)	54.	6187088	02/01/2001	Okumura
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Examiner *Colleen E. Graf*Date Considered *23 March 2007*

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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Examiner *Colleen DeRuf*Date Considered *23 March 2007*

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(CR)	80.	6621044	09/01/2003	Jain et al.
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(CR)	95.	6563077	05/13/2003	Im

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Examiner *Colleen E. O'Farrell*Date Considered *23 March 2007*

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	96.	6582827	06/24/2003	Im
<i>CR</i>	97.	6830993	12/14/2004	Im et al.

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Examiner

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		Examiner <i>Rodgers</i>	

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					Yes	No
CR	98.	681316	08/11/1995	EP		
CR	99.	1067593	10/01/2001	EP		
CR	100.	655774	07/17/1996	EP		
CR	101.	2338343	12/15/1999	GB		
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CR	106.	6283422	10/07/1994	JP		No
CR	107.	7176757	07/14/1995	JP		No
CR	108.	11064883	03/05/1999	JP		No
CR	109.	04033327		JP		No
CR	110.	2001023920	01/26/2001	JP		
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CR	112.	9824118	06/04/1998	WO		

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Examiner *Colleen E. Geigle*Date Considered *23 March 2007*

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Exam Initial	No.	Document No.	Publication Date	Country	Translation Yes No
(P)	113.	9931719	06/24/1999	WO	<u>No</u>
(C)	114.	0014784	03/16/2000	WO	
(C)	115.	0118854	03/15/2001	WO	
(C)	116.	0118855	03/15/2001	WO	
(C)	117.	0171786	09/27/2001	WO	
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(C)	122.	03046965	06/05/2003	WO	
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(C)	128.	04017381	02/26/2004	WO	

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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
<i>cc</i>	129.	04017380	02/26/2004	WO		
<i>cp</i>	130.	04075263	08/19/2003	WO		

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
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(P)	142.	K.H. Weiner et al., "Ultrashallow Junction Formation Using Projection Gas Immersion Laser Doping (PGILD)," A Verdant Technologies Technical Brief, Aug. 20, 1997.	
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(C)	148.	S.D. Brotherton, "Polycrystalline Silicon Thin Film Transistors," 10 Semicond. Sci. Tech., pp. 721-738 (1995).	
(C)	149.	H. Watanabe et al., "Crystallization Process of Polycrystalline Silicon by KrF Excimer Laser Annealing," 33 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4491-98 (1994). -	
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(C)	152.	Im <i>et al.</i> , "Phase Transformation Mechanisms Involved in Excimer Laser Crystallization of Amorphous Silicon Films," Appl. Phys. Lett., Vol. 63 (14), p. 1969 (1993).	
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